

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"5231038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:23
L2	2	"6455376".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:26
L3	16	(silicon near oxide) with (deep near3 junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:29
L4	40	(silicon near oxide) same (deep near3 junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:31
L5	669	(silicon near oxide) and (deep near3 junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:32
L6	15006	(silicon near oxide) and (deep near3 junction or shallow)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:32
L7	4596	(silicon near oxide) and (deep near3 junction or shallow near3 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:32
L8	1870	7 and (channel near region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:33
L9	1382	8 and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:33

L10	368	9 and (gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:39
L11	1	10 and (electrode) with (t-shape or t near shape)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:34
L12	71	10 and (silicon near oxide) near3 (spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 20:40